

East : USPBUSPT, WPID, JPO

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2554642	etch\$ or patern\$ or remov\$	US-PGPUB; USPAT	OR	ON	2005/11/18 15:02
L2	647452	peripheral	US-PGPUB; USPAT	OR	ON	2005/11/18 15:03
L3	737117	cell	US-PGPUB; USPAT	OR	ON	2005/11/18 15:03
L4	505506	resist or photoresist or mask or photomask	US-PGPUB; USPAT	OR	ON	2005/11/18 15:03
L5	108528	guard\$	US-PGPUB; USPAT	OR	ON	2005/11/18 15:03
L6	1882	1 same 2 same 3 same 4	US-PGPUB; USPAT	OR	ON	2005/11/18 14:52
L7	29	5 same 6	US-PGPUB; USPAT	OR	ON	2005/11/18 14:52
L8	687758	(etch\$ or patern\$ or remov\$).clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L9	183310	peripheral.clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L10	248746	cell.clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L11	108586	(resist or photoresist or mask or photomask).clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L12	18546	guard\$.clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L13	10	8 and 9 and 10 and 11 and 12	US-PGPUB; USPAT	OR	ON	2005/11/18 14:57
L14	2	13 not 7	US-PGPUB; USPAT	OR	ON	2005/11/18 14:57
L15	1715892	etch\$ or patern\$ or remov\$	JPO; DERWENT	OR	ON	2005/11/18 15:02
L16	535527	peripheral	JPO; DERWENT	OR	ON	2005/11/18 15:03
L17	611950	cell	JPO; DERWENT	OR	ON	2005/11/18 15:03
L18	351919	resist or photoresist or mask or photomask	JPO; DERWENT	OR	ON	2005/11/18 15:03
L19	49142	guard\$	JPO; DERWENT	OR	ON	2005/11/18 15:03
L20	682	15 and 16 and 17 and 18	JPO; DERWENT	OR	ON	2005/11/18 15:03
L21	8	20 and 19	JPO; DERWENT	OR	ON	2005/11/18 15:03

East of USPTO USPTW PID JPO

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2554642	etch\$ or patern\$ or remov\$	US-PGPUB; USPAT	OR	ON	2005/11/18 16:57
L2	647452	peripheral	US-PGPUB; USPAT	OR	ON	2005/11/18 16:57
L3	737117	cell	US-PGPUB; USPAT	OR	ON	2005/11/18 16:58
L4	505506	resist or photoresist or mask or photomask	US-PGPUB; USPAT	OR	ON	2005/11/18 16:58
L5	108528	guard\$	US-PGPUB; USPAT	OR	ON	2005/11/18 17:00
L6	1882	1 same 2 same 3 same 4	US-PGPUB; USPAT	OR	ON	2005/11/18 14:52
L7	29	5 same 6	US-PGPUB; USPAT	OR	ON	2005/11/18 15:14
L8	687758	(etch\$ or patern\$ or remov\$).clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L9	183310	peripheral.clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L10	248746	cell.clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L11	108586	(resist or photoresist or mask or photomask).clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L12	18546	guard\$.clm.	US-PGPUB; USPAT	OR	ON	2005/11/18 14:56
L13	10	8 and 9 and 10 and 11 and 12	US-PGPUB; USPAT	OR	ON	2005/11/18 14:57
L14	2	13 not 7	US-PGPUB; USPAT	OR	ON	2005/11/18 14:57
L15	1715892	etch\$ or patern\$ or remov\$	JPO; DERWENT	OR	ON	2005/11/18 15:02
L16	535527	peripheral	JPO; DERWENT	OR	ON	2005/11/18 15:03
L17	611950	cell	JPO; DERWENT	OR	ON	2005/11/18 15:03
L18	351919	resist or photoresist or mask or photomask	JPO; DERWENT	OR	ON	2005/11/18 15:03
L19	49142	guard\$	JPO; DERWENT	OR	ON	2005/11/18 15:03
L20	682	15 and 16 and 17 and 18	JPO; DERWENT	OR	ON	2005/11/18 15:03
L21	8	20 and 19	JPO; DERWENT	OR	ON	2005/11/18 15:03
L22	4088471	1st or first or 1 st	US-PGPUB; USPAT	OR	ON	2005/11/18 16:58

L23	3564521	2nd or second or 2 nd	US-PGPUB; USPAT	OR	ON	2005/11/18 16:59
L24	969084	dielectric or insulator or oxide or sio or "sio2" or nitride	US-PGPUB; USPAT	OR	ON	2005/11/18 16:59
L25	270604	22 with 24	US-PGPUB; USPAT	OR	ON	2005/11/18 16:29
L26	167677	23 with 24	US-PGPUB; USPAT	OR	ON	2005/11/18 16:29
L27	170048	1 with 25	US-PGPUB; USPAT	OR	ON	2005/11/18 16:30
L28	37914	1 with 26	US-PGPUB; USPAT	OR	ON	2005/11/18 16:30
L29	745	6 same 27 same 28	US-PGPUB; USPAT	OR	ON	2005/11/18 16:30
L30	143	29 same spacer	US-PGPUB; USPAT	OR	ON	2005/11/18 16:52
L31	108213	"1st layer" or "1 st layer" or "first layer" or "1st insulator" or "1 st insulator" or "first insulator" or "1st dielectric" or "1 st dielectric" or "first dielectric"	US-PGPUB; USPAT	OR	ON	2005/11/18 17:03
L32	109201	"2nd layer" or "2 nd layer" or "second layer" or "2nd insulator" or "2 nd insulator" or "second insulator" or "2nd dielectric" or "2 nd dielectric" or "second dielectric"	US-PGPUB; USPAT	OR	ON	2005/11/18 17:04
L33	56	6 same 31 same 32	US-PGPUB; USPAT	OR	ON	2005/11/18 16:35
L34	17601	"1st mask" or "1 st mask" or "first mask" or "1st resist" or "1 st resist" or "first resist" or "1st photoresist" or "1 st photoresist" or "first photoresist"	US-PGPUB; USPAT	OR	ON	2005/11/18 17:04
L35	16574	"2nd resist" or "2 nd resist" or "second resist" or "2nd photoresist" or "2 nd photoresist" or "second photoresist" or "2nd mask" or "2 nd mask" or "second mask"	US-PGPUB; USPAT	OR	ON	2005/11/18 17:04
L36	59	6 same 34 same 35	US-PGPUB; USPAT	OR	ON	2005/11/18 16:39
L37	112	33 or 36	US-PGPUB; USPAT	OR	ON	2005/11/18 16:39
L38	16	37 same spacer	US-PGPUB; USPAT	OR	ON	2005/11/18 16:42
L39	96	37 not 38	US-PGPUB; USPAT	OR	ON	2005/11/18 16:42
L40	121	30 not (7 or 13 or 37)	US-PGPUB; USPAT	OR	ON	2005/11/18 16:53

L41	10	30 same (isotropic\$ or wet or fluid or liquid or bath or aq or aqueous or aques)	US-PGPUB; USPAT	OR	ON	2005/11/18 16:54
L42	8	40 and 41	US-PGPUB; USPAT	OR	ON	2005/11/18 16:54
L43	12	30 same (hf or acid or hydrofluoric or basic or alkaline or ph or boe or bhf)	US-PGPUB; USPAT	OR	ON	2005/11/18 16:55
L44	12	40 and 43	US-PGPUB; USPAT	OR	ON	2005/11/18 16:55
L45	17	42 or 44	US-PGPUB; USPAT	OR	ON	2005/11/18 16:56
L46	104	40 not 45	US-PGPUB; USPAT	OR	ON	2005/11/18 16:56
L47	1715892	etch\$ or patern\$ or remov\$	JPO; DERWENT	OR	ON	2005/11/18 16:57
L48	535527	peripheral	JPO; DERWENT	OR	ON	2005/11/18 16:57
L49	611950	cell	JPO; DERWENT	OR	ON	2005/11/18 16:58
L50	351919	resist or photoresist or mask or photomask	JPO; DERWENT	OR	ON	2005/11/18 16:58
L51	2173412	1st or first or 1 st	JPO; DERWENT	OR	ON	2005/11/18 16:58
L52	2014724	2nd or second or 2 nd	JPO; DERWENT	OR	ON	2005/11/18 16:59
L53	1106077	dielectric or insulator or oxide or sio or "sio2" or nitride	JPO; DERWENT	OR	ON	2005/11/18 16:59
L54	49142	guard\$	JPO; DERWENT	OR	ON	2005/11/18 17:00
L55	682	47 and 48 and 49 and 50	JPO; DERWENT	OR	OFF	2005/11/18 17:00
L56	8	55 and 54	JPO; DERWENT	OR	OFF	2005/11/18 17:01
L57	317	55 and 51 and 52	JPO; DERWENT	OR	OFF	2005/11/18 17:01
L58	98057	47 with 51	JPO; DERWENT	OR	OFF	2005/11/18 17:02
L59	89838	47 with 52	JPO; DERWENT	OR	OFF	2005/11/18 17:02
L60	187	57 and 58 and 59	JPO; DERWENT	OR	OFF	2005/11/18 17:02
L61	40772	47 with 51 with (53 or layer or film)	JPO; DERWENT	OR	ON	2005/11/18 17:02
L62	38664	47 with 52 with (53 or layer or film)	JPO; DERWENT	OR	ON	2005/11/18 17:03

L63	173	60 and 61 and 62	JPO; DERWENT	OR	ON	2005/11/18 17:03
L64	44934	"1st layer" or "1 st layer" or "first layer" or "1st insulator" or "1 st insulator" or "first insulator" or "1st dielectric" or "1 st dielectric" or "first dielectric"	JPO; DERWENT	OR	ON	2005/11/18 17:03
L65	43506	"2nd layer" or "2 nd layer" or "second layer" or "2nd insulator" or "2 nd insulator" or "second insulator" or "2nd dielectric" or "2 nd dielectric" or "second dielectric"	JPO; DERWENT	OR	ON	2005/11/18 17:04
L66	5837	"1st mask" or "1 st mask" or "first mask" or "1st resist" or "1 st resist" or "first resist" or "1st photoresist" or "1 st photoresist" or "first photoresist"	JPO; DERWENT	OR	ON	2005/11/18 17:04
L67	5915	"2nd resist" or "2 nd resist" or "second resist" or "2nd photoresist" or "2 nd photoresist" or "second photoresist" or "2nd mask" or "2 nd mask" or "second mask"	JPO; DERWENT	OR	ON	2005/11/18 17:04
L68	77	55 and (64 or 66) and (65 or 67)	JPO; DERWENT	OR	ON	2005/11/18 17:05
L69	84	56 or 68	JPO; DERWENT	OR	ON	2005/11/18 17:16
L70	118	63 not 69	JPO; DERWENT	OR	ON	2005/11/18 17:16